TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

TPCA8036-H

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 13 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) = $2.8 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 113 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode: $V_{th} = 1.3 \text{ to } 2.3 \text{ V (VDS} = 10 \text{ V, ID} = 0.5 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	30	V	
Drain-gate voltage (R	$GS = 20 \text{ k}\Omega$	V_{DGR}	30	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	ΙD	38	Α	
Drain current	Pulsed (Note 1) I _{DP} 114 esipation (Tc=25°C) P _D 45	114	, ,		
Drain power dissipation	on (Tc=25°C)	P_{D}	45	W	
Drain power dissipation	on $(t = 10 s)$ (Note 2a)	P_{D}	2.8	W	
Drain power dissipation	on $(t = 10 s)$ (Note 2b)	P _D	1.6	W	
Single-pulse avalanch	ne energy (Note 3)	E _{AS}	188	mJ	
Avalanche current		I _{AR}	38	Α	
Repetitive avalanche	energy c = 25°C) (Note 4)	E _{AR}	0.18	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature	range	T _{stg}	-55 to 150	°C	

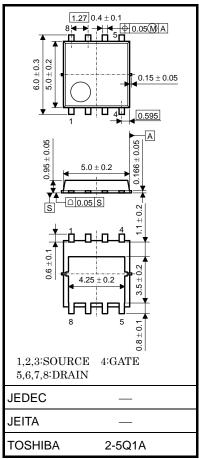
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

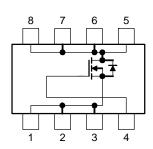
This transistor is an electrostatic-sensitive device. Handle with care.





Weight: 0.069 g (typ.)

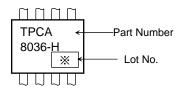
Circuit Configuration



Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient $(t=10 \; s) \eqno(Note \; 2a)$	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W

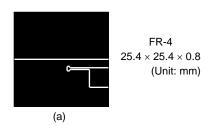
Marking (Note 5)

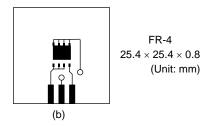


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

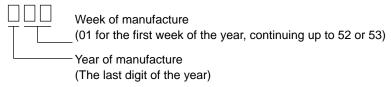




Note 3: $V_{DD} = 24~V,~T_{ch} = 25^{\circ}C$ (initial), L = 100 $\mu H,~R_G = 25~\Omega,~I_{AR} = 38~A$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



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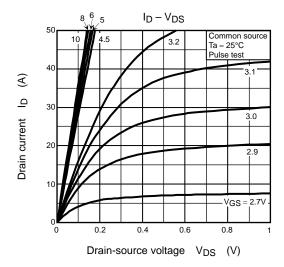
Electrical Characteristics (Ta = 25°C)

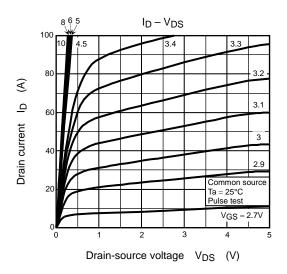
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V		_	10	μА
Droin course bro	akdawa valtaga	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	— ±100	V	
Drain-source breakdown voltage		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_	V
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, I_{D} = 0.5 \text{ mA}$	1.3	_	2.3	V
Droin course ON	rociatanos	P== (==)	V _{GS} = 4.5 V, I _D = 19 A	_	3.4	4.8	0
Drain-source ON-resistance		KDS (ON)	V _{GS} = 10 V, I _D = 19 A	_	2.8	4.2	mΩ
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 19 A	57	113	_	S
Input capacitance	e	C _{iss}		_	3500	4600	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	230	370	pF
Output capacitance		C _{oss}		_	690	_	
Gate resistance		rg	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	1.0	1.5	Ω
	Rise time	t _r	$\begin{array}{c} V_{(BR)DSS} & I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V} \\ V_{(BR)DSX} & I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V} \\ V_{th} & V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA} \\ I_{DS}(ON) & V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A} \\ V_{GS} = 10 \text{ V}, I_D = 19 \text{ A} \\ V_{GS} = 10 \text{ V}, I_D = 19 \text{ A} \\ V_{DS} = 10 \text{ V}, I_D = 19 \text{ A} \\ V_{DS} = 10 \text{ V}, I_D = 19 \text{ A} \\ V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, f = 1 \text{ MHz} \\ V_{DS} \approx 15 \text{ V} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DS} \approx 10 \text{ V}, V_{DS} \approx 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A} \\ V_{DD} \approx 24 \text{ V}, V_{DD} \approx 24 \text{ V},$	_	4.7	_	
Cuitabina tima	Turn-on time	t _{on}]			
Switching time	Fall time	t _f	27.7.4 W W W W W W W W W W W W W W W W W W W	_	7.7		ns
	Turn-off time	t _{off}	55	_	48	_	
Total gate charge)	0	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A}$		50	_	
(gate-source plus	gate-drain)	Q_{g}	V _{DD} ≈ 24 V, V _{GS} = 5 V, I _D = 38 A		26	_	
Gate-source charge 1		Q _{gs1}		_	11	_	nC
Gate-drain ("Miller") charge		Q _{gd}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38 \text{ A}$	_	7.8	_	
Gate switch char	ge	Q _{SW}	1	_	13	26 — 11 — 7.8 —	

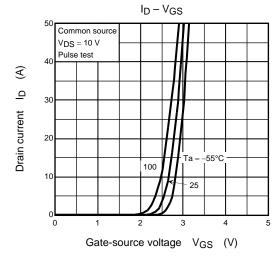
Source-Drain Ratings and Characteristics (Ta = 25°C)

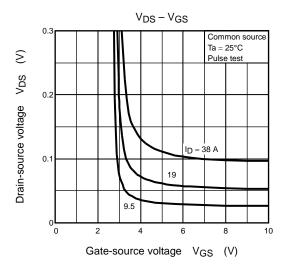
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	_	_	_	114	Α
Forward voltage (diode)			V _{DSF}	$I_{DR} = 38 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.2	V

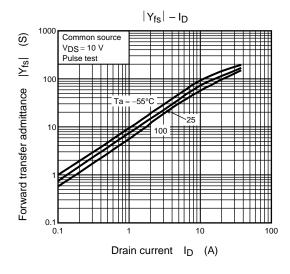
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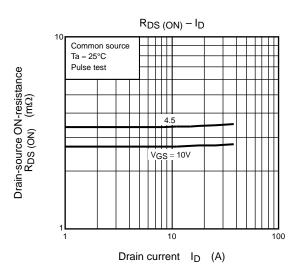




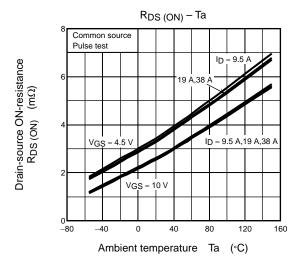


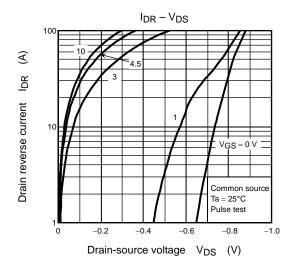


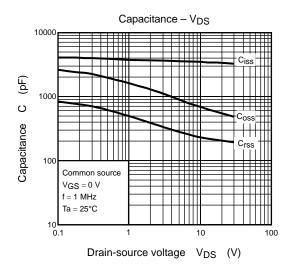


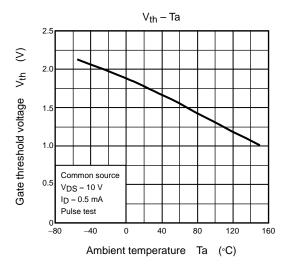


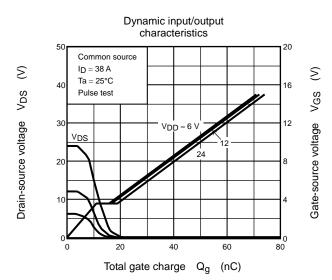
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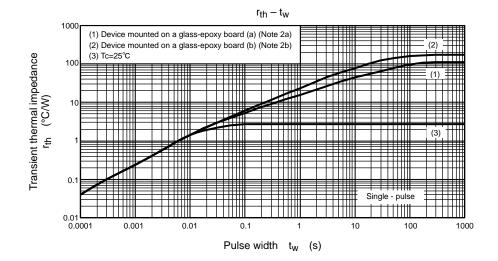


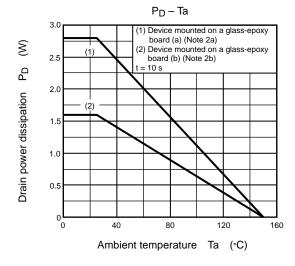


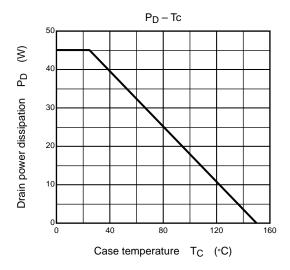


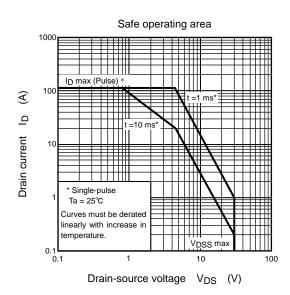


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